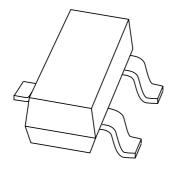
DISCRETE SEMICONDUCTORS

DATA SHEET



MMBT3906 PNP switching transistor

Product data sheet Supersedes data of 2000 Apr 11 2003 Mar 18



PNP switching transistor

MMBT3906

FEATURES

- Collector current capability I_C = −200 mA
- Collector-emitter voltage $V_{CEO} = -40 \text{ V}$.

APPLICATIONS

· General switching and amplification.

DESCRIPTION

PNP switching transistor in a SOT23 plastic package. NPN complement: MMBT3904.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾		
MMBT3906	7B*		

Note

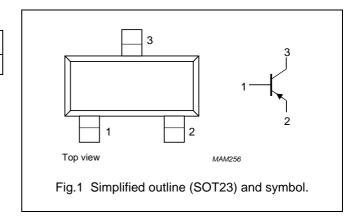
- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-40	V
I _C	collector current (DC)	-200	mA

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-40	V
V_{CEO}	collector-emitter voltage	open base	_	-40	V
V _{EBO}	emitter-base voltage	open collector	_	-6	V
I _C	collector current (DC)		_	-200	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -30 V	_	-50	nA
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -6 \text{ V}$	_	-50	nA
h _{FE}	DC current gain	V _{CE} = −1 V; see Fig.2			
		$I_{\rm C} = -0.1 \text{mA}$	60	_	
		$I_C = -1 \text{ mA}$	80	_	
		$I_{\rm C} = -10 \; {\rm mA}$	100	300	
		$I_{\rm C} = -50 \; {\rm mA}$	60	_	
		$I_{\rm C} = -100 \text{ mA}$	30	_	
V _{CEsat}	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	_	-250	mV
	voltage	$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	_	-400	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	_	-850	mV
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	_	-950	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -5 \text{ V}$; $f = 1 \text{ MHz}$	_	4.5	pF
C _e	emitter capacitance	$I_C = I_c = 0$; $V_{EB} = -500 \text{ mV}$; $f = 1 \text{ MHz}$	_	10	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -20 \text{ V};$ f = 100 MHz	250	_	MHz
F	noise figure	$I_C = -100 \mu A$; $V_{CE} = -5 V$; $R_S = 1 kΩ$; $f = 10 Hz$ to 15.7 kHz	-	4	dB
Switching ti	mes (between 10% and 90% lev	els); see Fig.7			
t _d	delay time	I _{Con} = -10 mA; I _{Bon} = -1 mA;	_	35	ns
t _r	rise time	I _{Boff} = 1 mA	_	35	ns
t _s	storage time		_	225	ns
t _f	fall time		_	75	ns

> -250 I_{C} (mA)

-200

-150

-100

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MHC460

(2)

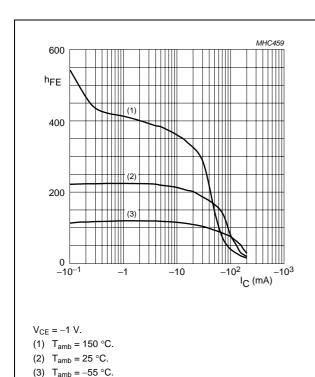
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(6) (7)

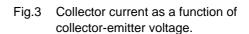
(8)

(9)

(10)



-50 $^{-8}$ $_{\text{CE}}^{-10}$ -2 -4 -6 $T_{amb} = 25 \, ^{\circ}C.$ (5) $I_B = -0.9 \text{ mA}.$ (1) $I_B = -1.5 \text{ mA}.$ (9) $I_B = -0.3 \text{ mA}.$ (10) $I_B = -0.15 \text{ mA}$. (2) $I_B = -1.35 \text{ mA}$. (6) $I_B = -0.75 \text{ mA}.$ (3) $I_B = -1.2 \text{ mA}.$ (7) $I_B = -0.6 \text{ mA}.$ (4) $I_B = -1.05 \text{ mA}.$ (8) $I_B = -0.45 \text{ mA}.$



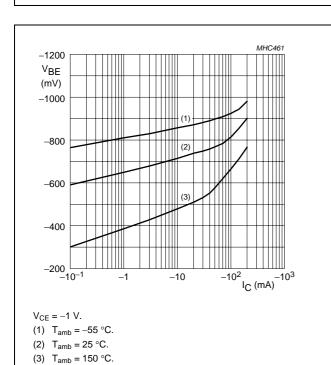
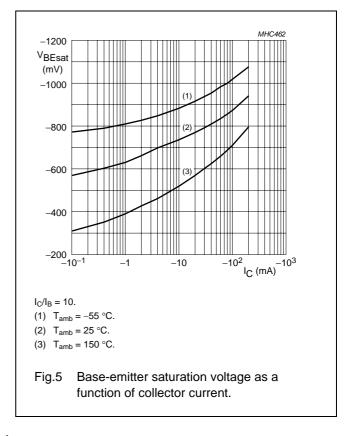


Fig.2 DC current gain; typical values.



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Fig.4 Base-emitter voltage as a function of

collector current.

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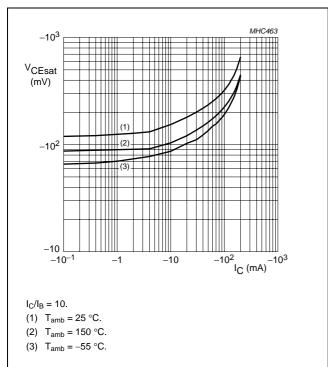
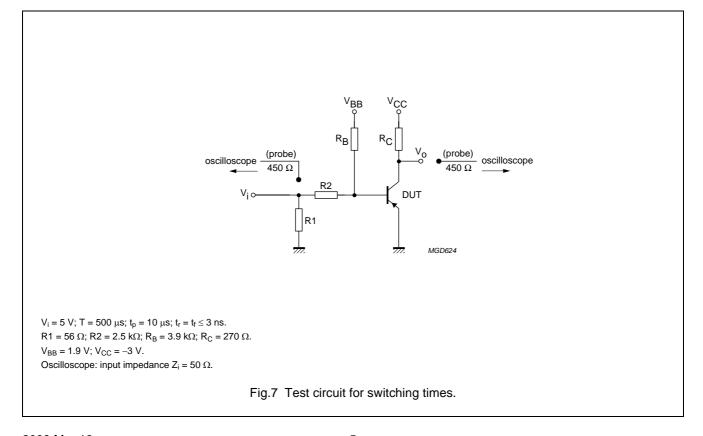


Fig.6 Collector-emitter saturation voltage as a function of collector current.



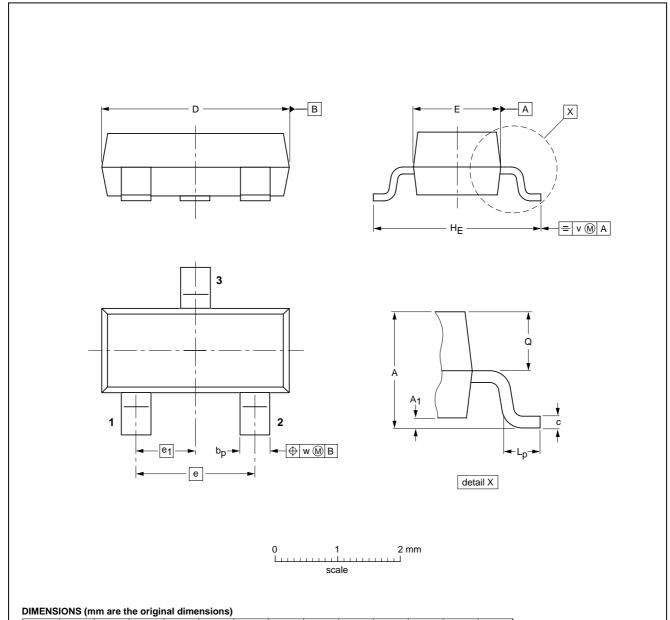
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



UNIT	Α	A ₁ max.	bp	С	D	E	е	e ₁	HE	L _p	Q	V	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT23		TO-236AB				-97-02-28 99-09-13

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PNP switching transistor

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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